

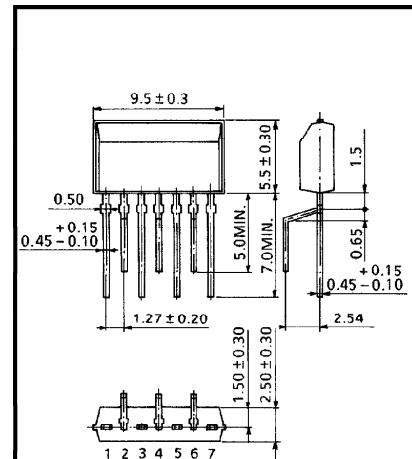
TOSHIBA DUAL FIELD EFFECT TRANSISTOR SILICON MONOLITHIC N CHANNEL JUNCTION TYPE

2SK389

LOW NOISE AUDIO AND DIFFERENTIAL AMPLIFIER APPLICATIONS.

Unit in mm

- 1 Chip Dual Type.
- Recommended for First Differential Stages of DC Amplifiers.
- Very High $|Y_{fs}|$: $|Y_{fs}|=20\text{mS}$ (Typ.)
($V_{DS}=10\text{V}$, $V_{GS}=0$, $f=1\text{kHz}$, $I_{DSS}=3\text{mA}$)
- Good Pair Characteristics
- High Breakdown Voltage : $V_{GDS}=-50\text{V}$ (Min.)
- Very Low Noise : $NF=0.5\text{dB}$ (Typ.)
($V_{DS}=10\text{V}$, $I_D=1\text{mA}$, $R_G=1\text{k}\Omega$, $f=1\text{kHz}$)
- High Input Impedance : $I_{GSS}=-1.0\text{nA}$ (Max.) ($V_{GS}=-30\text{V}$)
- Complementary to 2SJ109



- 1. DRAIN 1
- 2. GATE 1
- 3. SOURCE 1
- 4. SUBSTRATE (Note 2)
- 5. SOURCE 2
- 6. GATE 2
- 7. DRAIN 2

JEDEC	—
EIAJ	—
TOSHIBA	2-10M1A

Weight : 0.37g (Typ.)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-50	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	200	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~125	$^\circ\text{C}$

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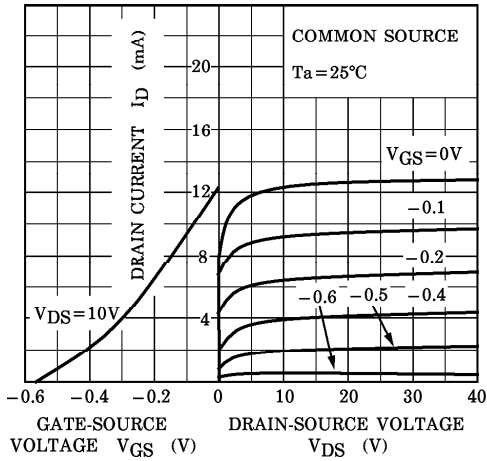
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Cut-off Current	I _{GSS}	V _{GS} = -30V, V _{DS} = 0	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	V (BR) GDS	V _{DS} = 0, I _G = -100μA	-50	—	—	V
Drain Current	I _{DSS} (Note 1)	V _{DS} = 10V, V _{GS} = 0	2.6	—	20	mA
Drain Current Ratio	I _{DSS} / I _{DSS} (small) (large)	V _{DS} = 10V, V _{GS} = 0	0.9	—	—	—
Gate-Source Cut-off Voltage	V _{GS} (OFF)	V _{DS} = 10V, I _D = 0.1μA	-0.15	—	-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, V _{GS} = 0 f = 1kHz, I _{DSS} = 3mA	8	20	—	mS
Forward Transfer Admittance Ratio	Y _{fs} / Y _{fs} (small) (large)	V _{DS} = 10V, V _{GS} = 0, f = 1kHz	0.9	—	—	—
Differential Gate-Source Voltage	V _{GS1} - V _{GS2}	V _{DS} = 10V, I _D = 1mA	—	—	20	mV
Input Capacitance	C _{iss}	V _{DS} = 10V, V _{GS} = 0, f = 1MHz	—	25	—	pF
Reverse Transfer Capacitance	C _{rss}	V _{GD} = -10V, I _D = 0, f = 1MHz	—	5.5	—	pF
Noise Figure	NF (1)	V _{DS} = 10V, R _G = 1kΩ I _D = 1mA, f = 10Hz	—	1.5	10	dB
	NF (2)	V _{DS} = 10V, R _G = 1kΩ I _D = 1mA, f = 1kHz	—	0.5	2	dB

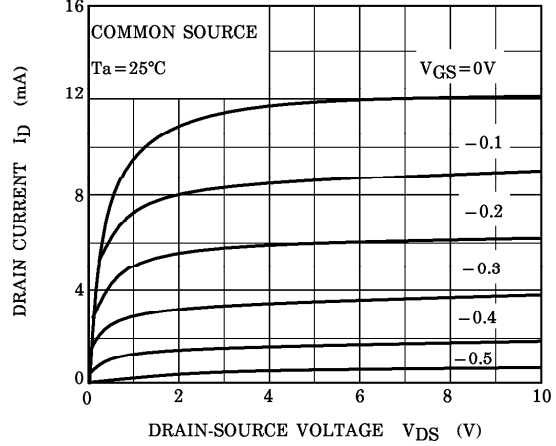
Note 1 : I_{DSS} Classification GR: 2.6~6.5mA, BL: 6~12mA, V: 10~20mA

Note 2 : Use the substrate lead with open.

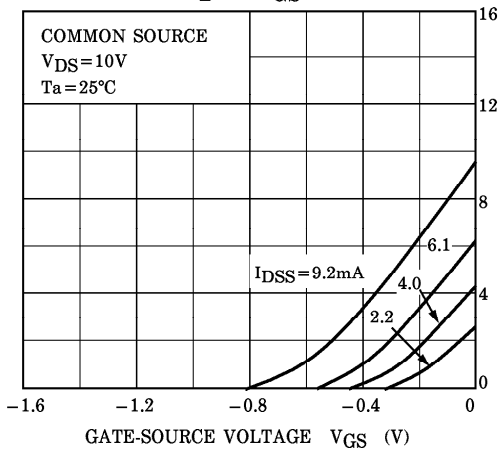
STATIC CHARACTERISTICS



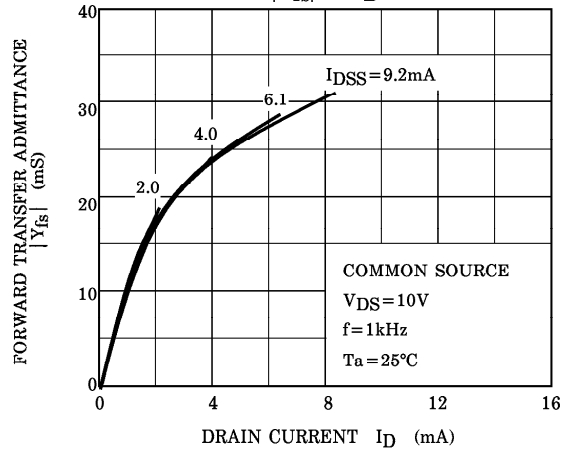
$I_D - V_{DS}$ (LOW VOLTAGE REGION)



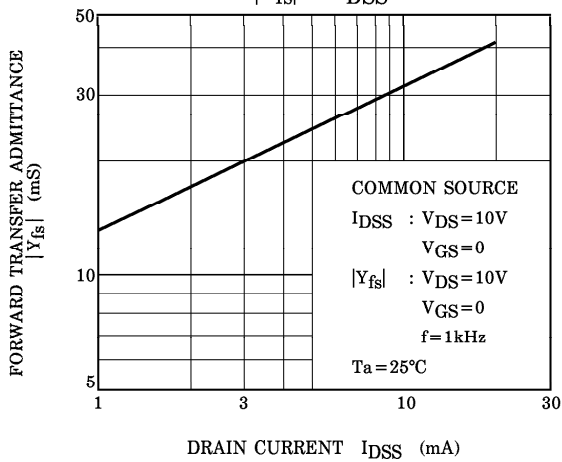
$I_D - V_{GS}$



$|Y_{fs}| - I_D$



$|Y_{fs}| - I_{DSS}$



VGS(OFF) - IDSS

